

# PMV213SN

$\mu$ TrenchMOS™ standard level FET

Rev. 02 — 19 February 2003

Product data

## 1. Product profile

### 1.1 Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

Product availability:

PMV213SN in SOT23.

### 1.2 Features

- Low on-state resistance in a small surface mount package.

### 1.3 Applications

- DC-to-DC primary side switching.

### 1.4 Quick reference data

- $V_{DS} \leq 100 \text{ V}$
- $I_D \leq 1.9 \text{ A}$
- $P_{tot} \leq 2 \text{ W}$
- $R_{DS(on)} \leq 250 \text{ m}\Omega$

## 2. Pinning information

Table 1: Pinning - SOT23 simplified outline and symbol

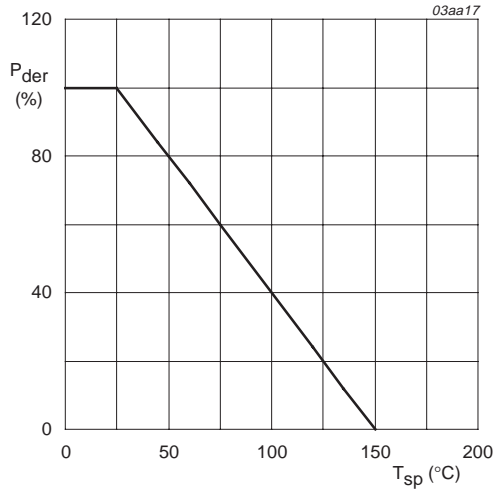
Pin	Description	Simplified outline	Symbol
1	gate (g)	<p>Top view MSB003</p> <p><b>SOT23</b></p>	<p>MBB076</p>
2	source (s)		
3	drain (d)		

### 3. Limiting values

**Table 2: Limiting values**

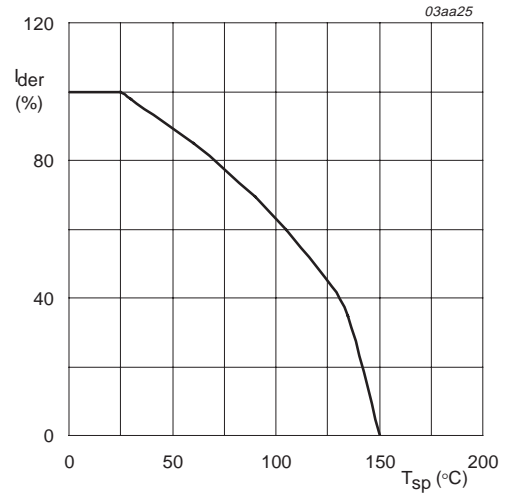
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	100	V
$V_{DGR}$	drain-gate voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	100	V
$V_{GS}$	gate-source voltage (DC)		-	$\pm 30$	V
$I_D$	drain current (DC)	$T_{sp} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <b>Figure 2 and 3</b>	-	1.9	A
		$T_{sp} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <b>Figure 2</b>	-	1.2	A
$I_{DM}$	peak drain current	$T_{sp} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <b>Figure 3</b>	-	7.6	A
$P_{tot}$	total power dissipation	$T_{sp} = 25\text{ °C}$ ; <b>Figure 1</b>	-	2	W
$T_{stg}$	storage temperature		-55	+150	°C
$T_j$	junction temperature		-55	+150	°C
<b>Source-drain diode</b>					
$I_S$	source (diode forward) current (DC)	$T_{sp} = 25\text{ °C}$	-	1.7	A
$I_{SM}$	peak source (diode forward) current	$T_{sp} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	6.9	A



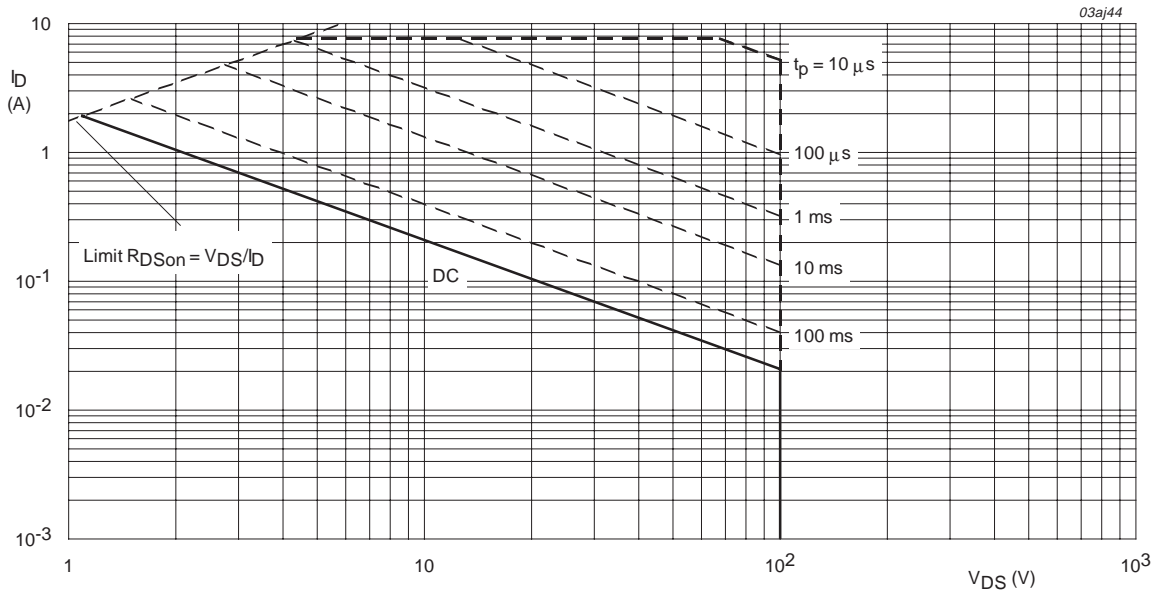
$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 1. Normalized total power dissipation as a function of solder point temperature.



$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature.



T<sub>sp</sub> = 25 °C; I<sub>DM</sub> is single pulse; V<sub>GS</sub> = 10V

Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

## 4. Thermal characteristics

Table 3: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	Figure 4	-	-	60	K/W

### 4.1 Transient thermal impedance

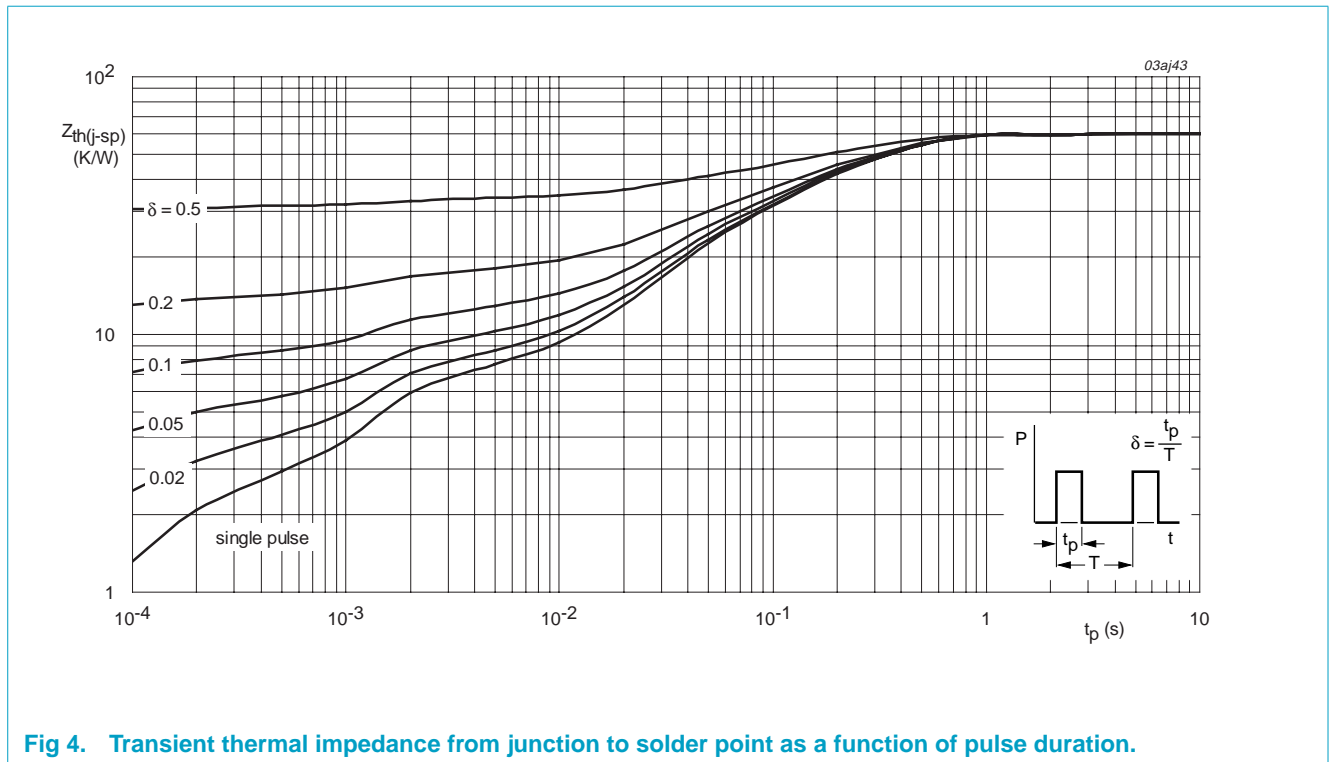
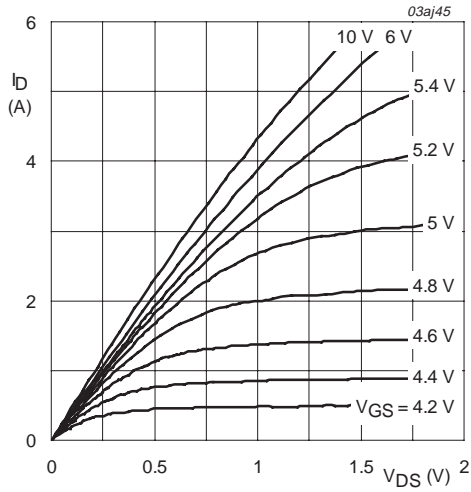


Fig 4. Transient thermal impedance from junction to solder point as a function of pulse duration.

## 5. Characteristics

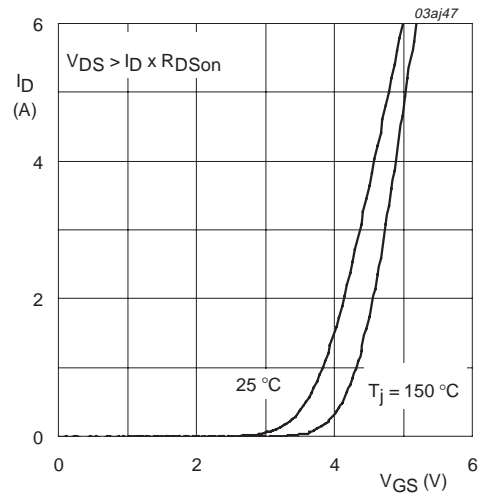
**Table 4: Characteristics**
 $T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$ ; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ }^\circ\text{C}$	100	-	-	V
		$T_j = -55\text{ }^\circ\text{C}$	90	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\text{ mA}$ ; $V_{DS} = V_{GS}$ ; <b>Figure 9</b> $T_j = 25\text{ }^\circ\text{C}$	2	3	4	V
		$T_j = 150\text{ }^\circ\text{C}$	1.2	-	-	V
		$T_j = -55\text{ }^\circ\text{C}$	-	-	4.4	V
$I_{DSS}$	drain-source leakage current	$V_{DS} = 100\text{ V}$ ; $V_{GS} = 0\text{ V}$ $T_j = 25\text{ }^\circ\text{C}$	-	-	1	$\mu\text{A}$
		$T_j = 150\text{ }^\circ\text{C}$	-	-	100	$\mu\text{A}$
$I_{GSS}$	gate-source leakage current	$V_{GS} = \pm 20\text{ V}$ ; $V_{DS} = 0\text{ V}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 0.5\text{ A}$ ; <b>Figure 7 and 8</b> $T_j = 25\text{ }^\circ\text{C}$	-	213	250	m $\Omega$
		$T_j = 150\text{ }^\circ\text{C}$	-	490	575	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{g(tot)}$	total gate charge	$I_D = 1.2\text{ A}$ ; $V_{DD} = 80\text{ V}$ ; $V_{GS} = 10\text{ V}$ ; <b>Figure 13</b>	-	7	-	nC
$Q_{gs}$	gate-source charge		-	1.4	-	nC
$Q_{gd}$	gate-drain (Miller) charge		-	2.5	-	nC
$C_{iss}$	input capacitance	$V_{GS} = 0\text{ V}$ ; $V_{DS} = 20\text{ V}$ ; $f = 1\text{ MHz}$ ; <b>Figure 11</b>	-	330	-	pF
$C_{oss}$	output capacitance		-	36	-	pF
$C_{rss}$	reverse transfer capacitance		-	22	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DD} = 50\text{ V}$ ; $R_L = 33\text{ }\Omega$ ; $V_{GS} = 10\text{ V}$ ; $R_G = 6\text{ }\Omega$	-	5.5	-	ns
$t_r$	rise time		-	5	-	ns
$t_{d(off)}$	turn-off delay time		-	9.5	-	ns
$t_f$	fall time		-	3	-	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain (diode forward) voltage	$I_S = 1.5\text{ A}$ ; $V_{GS} = 0\text{ V}$ ; <b>Figure 12</b>	-	0.83	1.2	V
$t_{rr}$	reverse recovery time	$I_S = 1.2\text{ A}$ ; $di_S/dt = -100\text{ A}/\mu\text{s}$ ; $V_{GS} = 0\text{ V}$	-	36	-	ns
$Q_r$	recovered charge		-	23	-	nC



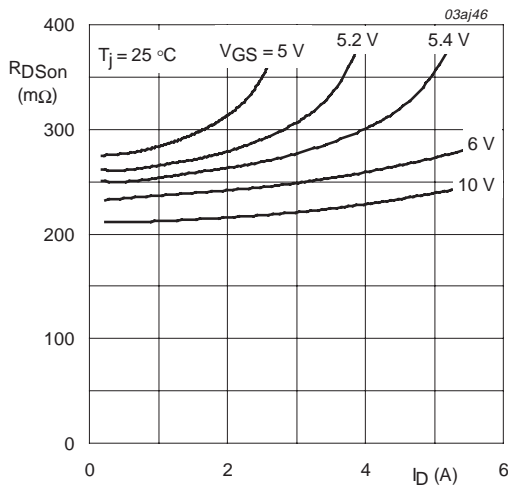
$T_j = 25\text{ °C}$

**Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.**



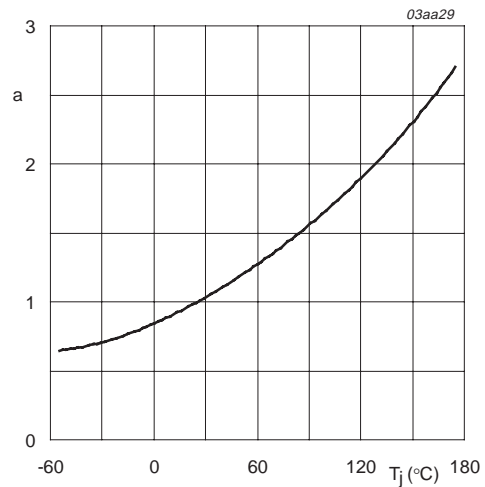
$T_j = 25\text{ °C}$  and  $150\text{ °C}$ ;  $V_{DS} > I_D \times R_{DSon}$

**Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.**



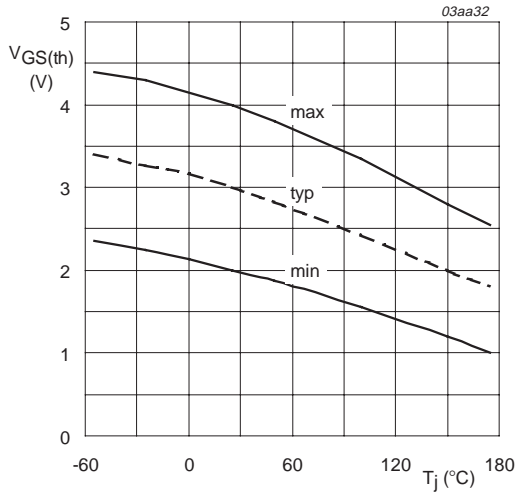
$T_j = 25\text{ °C}$

**Fig 7. Drain-source on-state resistance as a function of drain current; typical values.**



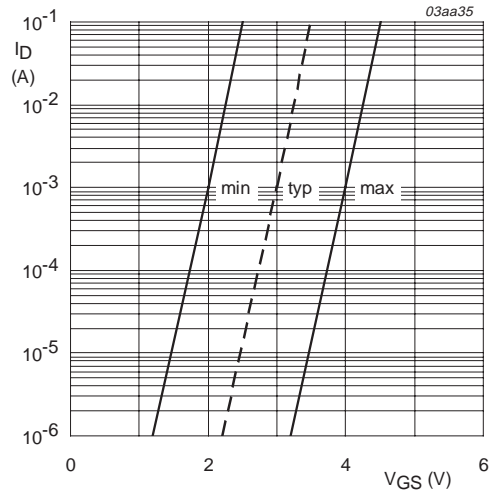
$$a = \frac{R_{DSon}}{R_{DSon(25\text{ °C})}}$$

**Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.**



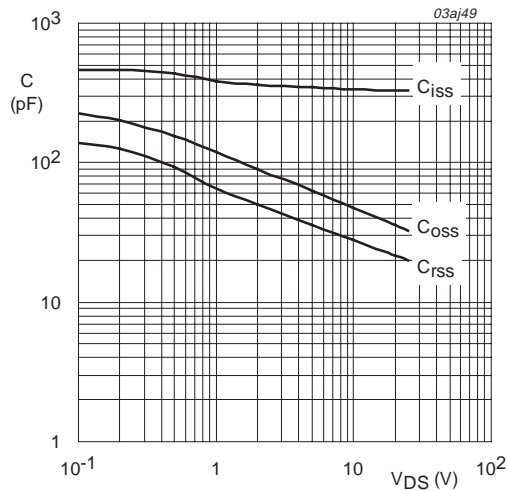
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

**Fig 9. Gate-source threshold voltage as a function of junction temperature.**



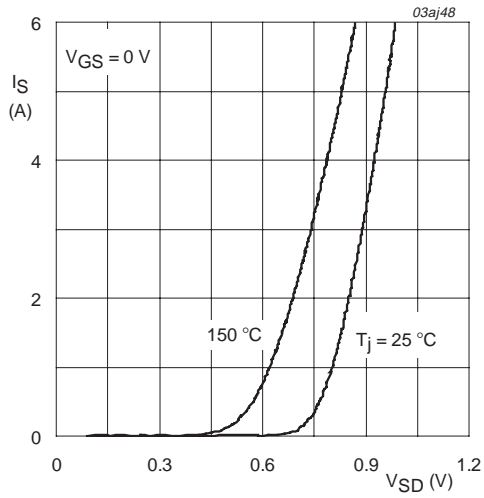
$T_j = 25 \text{ °C}$

**Fig 10. Sub-threshold drain current as a function of gate-source voltage.**



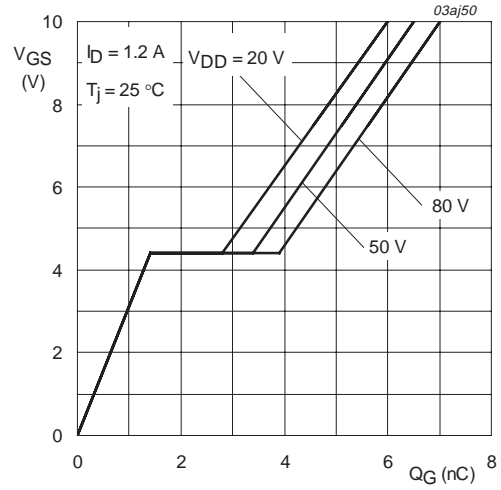
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

**Fig 11. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.**



$T_j = 25^\circ\text{C}$  and  $150^\circ\text{C}$ ;  $V_{GS} = 0$  V

**Fig 12. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.**



$I_D = 1.2$  A;  $V_{DD} = 20$  V,  $50$  V,  $80$  V

**Fig 13. Gate-source voltage as a function of gate charge; typical values.**



6. Package outline

Plastic surface mounted package; 3 leads

SOT23

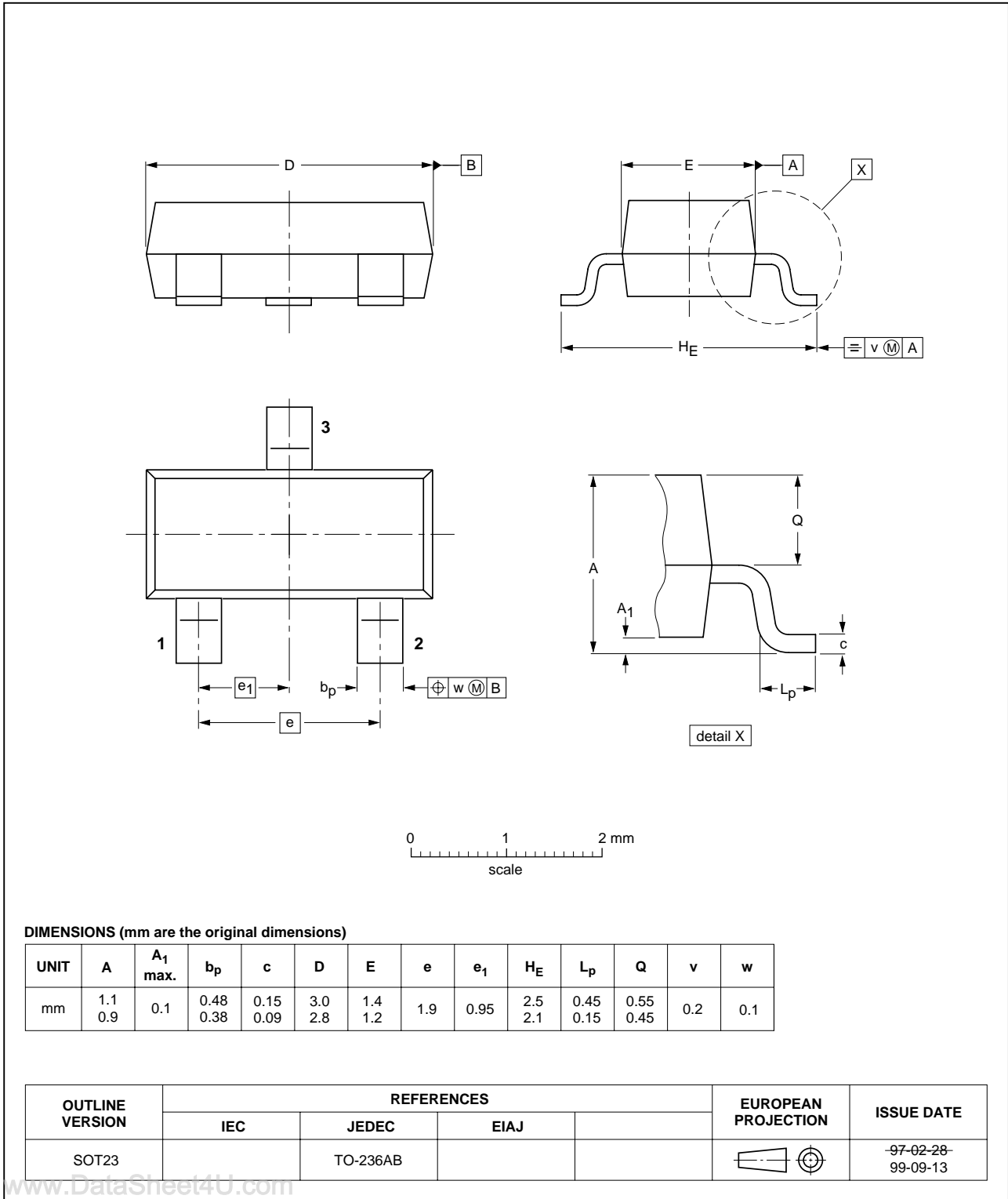


Fig 14. SOT23.

## 7. Revision history

Table 5: Revision history

Rev	Date	CPCN	Description
02	20030219	-	<b>Product data (9397 750 11128)</b> Modifications: <ul style="list-style-type: none"> <li>• Section 1.4 “Quick reference data” <math>I_D</math> modified due to improved <math>R_{th}</math>.</li> <li>• Section 1.4 “Quick reference data” <math>P_{tot}</math> modified due to improved <math>R_{th}</math>.</li> <li>• Section 3 “Limiting values” <math>I_D</math>, <math>I_{DM}</math>, <math>P_{tot}</math>, <math>I_S</math>, <math>I_{SM}</math> modified due to improved <math>R_{th}</math>.</li> <li>• Section 3 “Limiting values” Figure 3 SOA graph modified due to improved <math>R_{th}</math>.</li> <li>• Section 4 “Thermal characteristics” <math>R_{th(j-sp)}</math> improved.</li> <li>• Section 4 “Thermal characteristics” Figure 4 to reflect the improvement in <math>R_{th(j-sp)}</math>.</li> </ul>
01	20030115	-	<b>Product data (9397 750 10893)</b>

## 8. Data sheet status

Level	Data sheet status <sup>[1]</sup>	Product status <sup>[2][3]</sup>	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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**Limiting values definition** — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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## Contact information

For additional information, please visit <http://www.semiconductors.philips.com>.

For sales office addresses, send e-mail to: [sales.addresses@www.semiconductors.philips.com](mailto:sales.addresses@www.semiconductors.philips.com).

Fax: +31 40 27 24825

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